

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC1904

DESCRIPTION

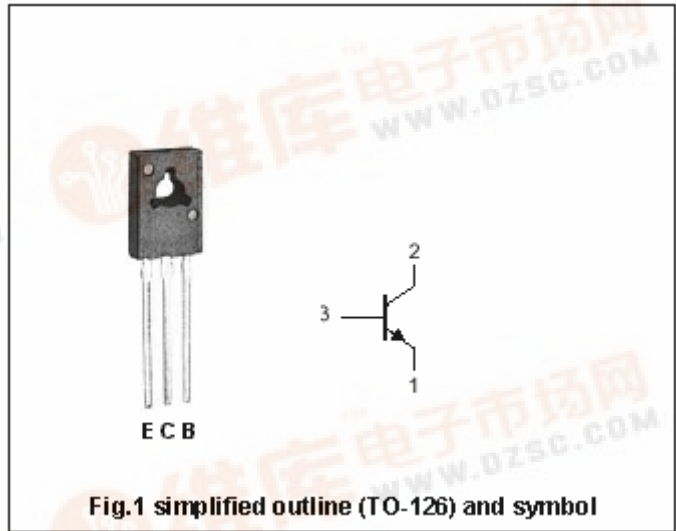
- With TO-126 package
- Complement to type 2SA899

APPLICATIONS

- For high frequency power amplification

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CB0}	Collector-base voltage	Open emitter	150	V
V _{CEO}	Collector-emitter voltage	Open base	150	V
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current (DC)		50mA	A
P _D	Total power dissipation	T _C =25°C	1	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =1mA; R _{BE} =∞	150			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =10 μ A ; I _E =0	150			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10 μ A ; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =10mA ; I _B =1mA			0.5	V
V _{BEsat}	Base-emitter saturation voltage	I _C =10mA ; I _B =1mA			1.0	V
I _{CBO}	Collector cut-off current	V _{CB} =140V; I _E =0			1	μ A
I _{EBO}	Emitter cut-off current	V _{EB} =4V; I _C =0			1	μ A
h _{FE}	DC current gain	I _C =10mA ; V _{CE} =5V	35		500	
C _{OB}	Output capacitance	I _E =0 ; V _{CB} =10V; f=1MHz		3		pF
f _T	Transition frequency	I _C =10mA ; V _{CE} =5V		70		MHz

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PACKAGE OUTLINE

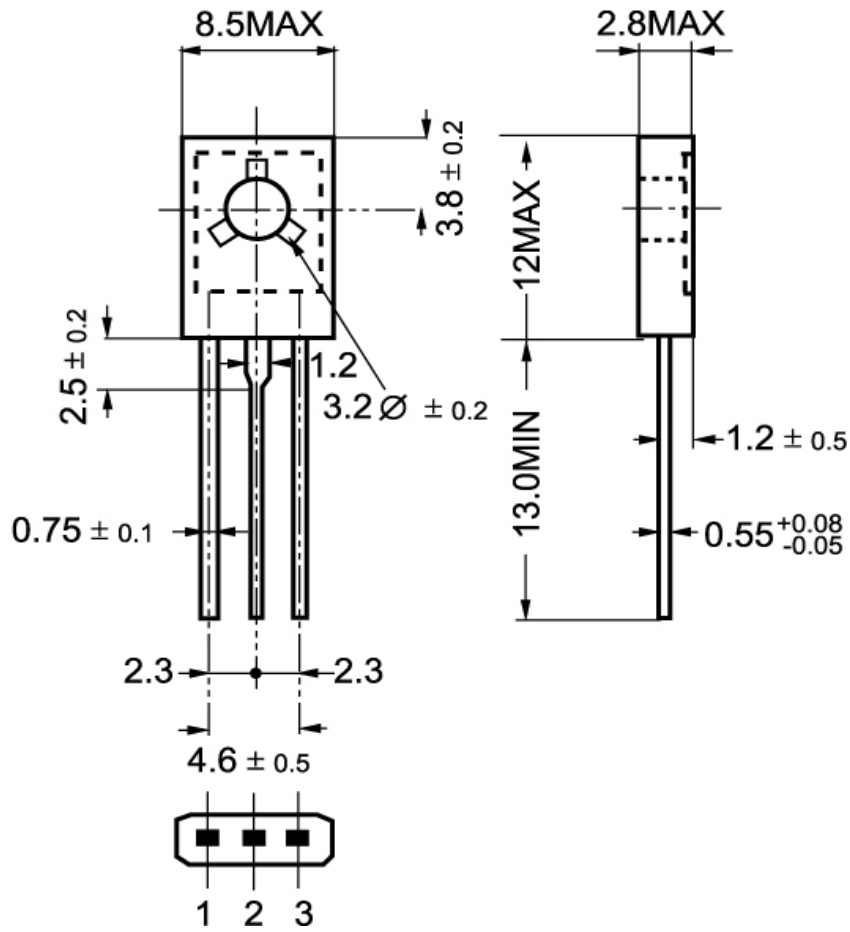


Fig.2 Outline dimensions